

IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming a silicon nitride film directly formed on the wiring;
- forming a first leveling film containing a siloxane structure on the silicon nitride film; **and**
- forming a second leveling film containing a siloxane structure on said first leveling film,

wherein said second leveling film is thicker than said first leveling film; and

forming a pixel electrode over the second leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the first and second leveling films.

2. (Currently Amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming a silicon nitride film covering a surface of the wiring;
- forming a first leveling film containing a siloxane structure on the silicon nitride film; **and**

forming a second leveling film containing a siloxane structure on said first leveling film,
wherein said second leveling film is thicker than said first leveling film; and

forming a pixel electrode over the second leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the first and second leveling films.

3. (Currently Amended) A method of fabricating a display device comprising the steps of:
forming a semiconductor film over a substrate;
forming an interlayer insulating film over the semiconductor film;
forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
forming a silicon nitride film deposited on the wiring;
forming a first leveling film containing a siloxane structure on the silicon nitride film; and
forming a second leveling film containing a siloxane structure on said first leveling film,
wherein said second leveling film is thicker than said first leveling film; and

forming a pixel electrode over the second leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the first and second leveling films.

4. (Currently Amended) A method of fabricating a display device comprising the steps of:
forming a semiconductor film over a substrate;
forming an interlayer insulating film over the semiconductor film;
forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
forming a silicon nitride oxide film directly formed on the wiring;

forming a first leveling film containing a siloxane structure on the silicon nitride oxide film;
and
forming a second leveling film containing a siloxane structure on said first leveling film,
wherein said second leveling film is thicker than said first leveling film; and
forming a pixel electrode over the second leveling film connecting to the wiring through a
second hole formed in the silicon nitride oxide film and the first and second leveling films.

5. (Currently Amended) A method of fabricating a display device comprising the steps of:
forming a semiconductor film over a substrate;
forming an interlayer insulating film over the semiconductor film;
forming a wiring connecting to the semiconductor film through a first hole in the interlayer
insulating film on the interlayer insulating film;
forming a silicon nitride oxide film covering a surface of the wiring;
forming a first leveling film containing a siloxane structure on the silicon nitride oxide film;
and
forming a second leveling film containing a siloxane structure on said first leveling film,
wherein said second leveling film is thicker than said first leveling film; and
forming a pixel electrode over the second leveling film connecting to the wiring through a
second hole formed in the silicon nitride oxide film and the first and second leveling films.

6. (Currently Amended) A method of fabricating a display device comprising the steps of:
forming a semiconductor film over a substrate;
forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a silicon nitride oxide film deposited on the wiring;

forming a first leveling film containing a siloxane structure on the silicon nitride oxide film;

and

forming a second leveling film containing a siloxane structure on said first leveling film, wherein said second leveling film is thicker than said first leveling film; and

forming a pixel electrode over the second leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the first and second leveling films.

7. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a silicon nitride film directly formed on the wiring;

forming a first leveling film containing a siloxane structure on the silicon nitride film;

forming a second leveling film containing a siloxane structure on said first leveling film, wherein said second leveling film is thicker than said first leveling film;

forming a pixel electrode connecting the wiring through a second hole in the silicon nitride film and the first and second leveling films over the second leveling film; and

forming an electro luminescence layer over the pixel electrode.

8. (Currently Amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming a silicon nitride oxide film directly formed on the wiring;
- forming a first leveling film containing a siloxane structure on the silicon nitride oxide film;
- forming a second leveling film containing a siloxane structure on said first leveling film,

wherein said second leveling film is thicker than said first leveling film;

- forming a pixel electrode connecting the wiring through a second hole in the silicon nitride oxide film and the first and second leveling films over the second leveling film;
- forming an electro luminescence layer over the pixel electrode; and
- forming a cathode made of a conductive film having a light-shielding property.

9. (Currently Amended) A method of fabricating a display device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming a silicon nitride oxide film directly formed on the wiring;
- forming a first leveling film containing a siloxane structure on the silicon nitride oxide film;
- forming a second leveling film containing a siloxane structure on said first leveling film,

wherein said second leveling film is thicker than said first leveling film;

forming a pixel electrode connecting the wiring through a second hole in the silicon nitride oxide film and the first and second leveling films over the second leveling film; and
forming an electro luminescence layer over the pixel electrode.

10. (Currently Amended) A method of fabricating a ~~display~~ semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;
forming an interlayer insulating film over the semiconductor film;
forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
forming a second insulating film comprising a material selected from the group consisting of silicon nitride and silicon nitride oxide ~~film~~ directly formed on the wiring;
forming a first leveling film formed by a spin coating method on the second insulating silicon nitride ~~nitride~~ film; and
forming a second leveling film by a spin coating method on said first leveling film, wherein said second leveling film is thicker than said first leveling film
~~forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film.~~

11. (Canceled)

12. (previously presented) The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and

a projector.

13. (Canceled)

14. (previously presented) The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. (Canceled)

16. (previously presented) The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. (Canceled)

18. (previously presented) The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (Canceled)

20. (previously presented) The method according to claim 5, wherein the display device is

used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (Canceled)

22. (previously presented) The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (Canceled)

24. (previously presented) The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (Canceled)

26. (previously presented) The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (Canceled)

28. (previously presented) The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29-30. (Canceled)

31. (Currently Amended) A method of fabricating a ~~display~~ semiconductor device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming a second insulating film comprising a material selected from the group consisting of silicon nitride and silicon nitride oxide ~~film~~ covering a surface of the wiring;
- forming a first leveling film ~~formed~~ by a spin coating method on the second insulating silicon nitride ~~nitride~~ film; and
- forming a second leveling film by a spin coating method on said first leveling film, wherein said second leveling film is thicker than said first leveling film
- ~~forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film.~~

32. (Canceled)

33. (Currently Amended) A method of fabricating a ~~display~~ semiconductor device comprising the steps of:

- forming a semiconductor film over a substrate;
- forming an interlayer insulating film over the semiconductor film;
- forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;
- forming ~~a silicon nitride~~ a second insulating film comprising a material selected from the group consisting of silicon nitride and silicon nitride oxide deposited on the wiring;
- forming a first leveling film ~~formed~~ by a spin coating method on the ~~silicon nitride~~ second insulating film; and
- forming a second leveling film by a spin coating method on said first leveling film, wherein said second leveling film is thicker than said first leveling film
- ~~forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film.~~

34. (Canceled)

35. (Previously Presented) The method according to claim 1, wherein the wiring is formed by a sputtering method.

36. (Previously Presented) The method according to claim 1, wherein the wiring comprises aluminum.

37. (Previously Presented) The method according to claim 1, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

38. (Previously Presented) The method according to claim 1, wherein the display device is a liquid crystal display device or an electro luminescence display device.

39. (Previously Presented) The method according to claim 1, wherein the silicon nitride film has a thickness of 50 to 500nm.

40. (Previously Presented) The method according to claim 1, wherein the silicon nitride film has a thickness of 200 to 300nm.

41. (Currently Amended) The method according to claim 1, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

42. (Canceled)

43. (Previously Presented) The method according to claim 1, wherein the pixel electrode is made of a conductive oxide film.

44. (Previously Presented) The method according to claim 2, wherein the wiring is formed by a sputtering method.

45. (Previously Presented) The method according to claim 2, wherein the wiring comprises aluminum.

46. (Previously Presented) The method according to claim 2, wherein the wiring is a three-layered laminate film containing a first titanium, an aluminum film and a second titanium.

47. (Previously Presented) The method according to claim 2, wherein the display device is a liquid crystal display device or an electro luminescence display device.

48. (Previously Presented) The method according to claim 2, wherein the silicon nitride film has a thickness of 50 to 500nm.

49. (Previously Presented) The method according to claim 2, wherein the silicon nitride film has a thickness of 200 to 300nm.

50. (Currently Amended) The method according to claim 2, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

51. (Canceled)

52. (Previously Presented) The method according to claim 2, wherein the pixel electrode is made of a conductive oxide film.

53. (Previously Presented) The method according to claim 3, wherein the wiring is formed by a sputtering method.

54. (Previously Presented) The method according to claim 3, wherein the wiring comprises aluminum.

55. (Previously Presented) The method according to claim 3, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

56. (Previously Presented) The method according to claim 3, wherein the display device is a liquid crystal display device or an electro luminescence display device.

57. (Previously Presented) The method according to claim 3, wherein the silicon nitride film has a thickness of 50 to 500nm.

58. (Previously Presented) The method according to claim 3, wherein the silicon nitride film has a thickness of 200 to 300nm.

59. (Currently Amended) The method according to claim 3, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

60. (Canceled)

61. (Previously Presented) The method according to claim 3, wherein the pixel electrode is made of a conductive oxide film.

62. (Previously Presented) The method according to claim 4, wherein the wiring is formed by a sputtering method.

63. (Previously Presented) The method according to claim 4, wherein the wiring comprises aluminum.

64. (Previously Presented) The method according to claim 4, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

65. (Previously Presented) The method according to claim 4, wherein the display device is a liquid crystal display device or an electro luminescence display device.

66. (Previously Presented) The method according to claim 4, wherein the silicon nitride oxide film has a thickness of 50 to 500nm.

67. (Previously Presented) The method according to claim 4, wherein the silicon nitride oxide film has a thickness of 200 to 300nm.

68. (Currently Amended) The method according to claim 4, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

69. (Canceled)

70. (Previously Presented) The method according to claim 4, wherein the pixel electrode is made of a conductive oxide film.

71. (Previously Presented) The method according to claim 5, wherein the wiring is formed by a sputtering method.

72. (Previously Presented) The method according to claim 5, wherein the wiring comprises aluminum.

73. (Previously Presented) The method according to claim 5, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

74. (Previously Presented) The method according to claim 5, wherein the display device is a liquid crystal display device or an electro luminescence display device.

75. (Previously Presented) The method according to claim 5, wherein the silicon nitride oxide film has a thickness of 50 to 500nm.

76. (Previously Presented) The method according to claim 5, wherein the silicon nitride oxide film has a thickness of 200 to 300nm.

77. (Currently Amended) The method according to claim 5, wherein the first leveling film has a thickness of 0.1 μm to 1.5 μm .

78. (Canceled)

79. (Previously Presented) The method according to claim 5, wherein the pixel electrode is made of a conductive oxide film.

80. (Previously Presented) The method according to claim 6, wherein the wiring is formed by a sputtering method.

81. (Previously Presented) The method according to claim 6, wherein the wiring comprises aluminum.

82. (Previously Presented) The method according to claim 6, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

83. (Previously Presented) The method according to claim 6, wherein the display device is a liquid crystal display device or an electro luminescence display device.

84. (Previously Presented) The method according to claim 6, wherein the silicon nitride oxide film has a thickness of 50 to 500nm.

85. (Previously Presented) The method according to claim 6, wherein the silicon nitride oxide film has a thickness of 200 to 300nm.

86. (Currently Amended) The method according to claim 6, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

87. (Canceled)

88. (Previously Presented) The method according to claim 6, wherein the pixel electrode is made of a conductive oxide film.

89. (Previously Presented) The method according to claim 7, wherein the wiring is formed by a sputtering method.

90. (Previously Presented) The method according to claim 7, wherein the wiring comprises aluminum.

91. (Previously Presented) The method according to claim 7, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

92. (Canceled)

93. (Previously Presented) The method according to claim 7, wherein the silicon nitride film has a thickness of 50 to 500nm.

94. (Previously Presented) The method according to claim 7, wherein the silicon nitride film has a thickness of 200 to 300nm.

95. (Currently Amended) The method according to claim 7, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

96. (Canceled)

97. (Previously Presented) The method according to claim 7, wherein the second hole is formed by a dry etching method.

98. (Previously Presented) The method according to claim 7, wherein the pixel electrode is made of a conductive oxide film.

99. (Previously Presented) The method according to claim 8, wherein the wiring is formed by a sputtering method.

100. (Previously Presented) The method according to claim 8, wherein the wiring comprises aluminum.

101. (Previously Presented) The method according to claim 8, wherein the wiring is a three-

layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

102. (Canceled)

103. (Previously Presented) The method according to claim 8, wherein the silicon nitride oxide film has a thickness of 50 to 500nm.

104. (Previously Presented) The method according to claim 8, wherein the silicon nitride oxide film has a thickness of 200 to 300nm.

105. (Currently Amended) The method according to claim 8, wherein the first leveling film has a thickness of 0.1 μm to 1.5 μm .

106. (Canceled)

107. (Previously Presented) The method according to claim 8, wherein the second hole is formed by a dry etching method.

108. (Previously Presented) The method according to claim 8, wherein the pixel electrode is made of a conductive oxide film.

109. (Previously Presented) The method according to claim 9, wherein the wiring is formed by a sputtering method.

110. (Previously Presented) The method according to claim 9, wherein the wiring comprises aluminum.

111. (Previously Presented) The method according to claim 9, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

112. (Canceled)

113. (Previously Presented) The method according to claim 9, wherein the silicon nitride oxide film has a thickness of 50 to 500nm.

114. (Previously Presented) The method according to claim 9, wherein the silicon nitride oxide film has a thickness of 200 to 300nm.

115. (Currently Amended) The method according to claim 9, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

116. (Canceled)

117. (Previously Presented) The method according to claim 9, wherein the second hole is formed by a dry etching method.

118. (Previously Presented) The method according to claim 9, wherein the pixel electrode is made of a conductive oxide film.

119. (Previously Presented) The method according to claim 10, wherein the wiring is formed by a sputtering method.

120. (Previously Presented) The method according to claim 10, wherein the wiring comprises aluminum.

121. (Previously Presented) The method according to claim 10, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

122. (Canceled)

123. (Currently Amended) The method according to claim 10, wherein the ~~silicon nitride~~ second insulating film has a thickness of 50 to 500nm.

124. (Currently Amended) The method according to claim 10, wherein the ~~silicon nitride~~ second insulating film has a thickness of 200 to 300nm.

125. (Currently Amended) The method according to claim 10, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

126. (Canceled)

127. (Currently Amended) The method according to claim 10, wherein each of the first and second leveling films comprises an inorganic spin on glass material.

128. (Canceled)

129. (Previously Presented) The method according to claim 31, wherein the wiring is formed by a sputtering method.

130. (Previously Presented) The method according to claim 31, wherein the wiring comprises aluminum.

131. (Previously Presented) The method according to claim 31, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

132. (Canceled)

133. (Currently Amended) The method according to claim 31, wherein the ~~silicon nitride~~ second insulating film has a thickness of 50 to 500nm.

134. (Currently Amended) The method according to claim 31, wherein the ~~silicon nitride~~ second insulating film has a thickness of 200 to 300nm.

135. (Currently Amended) The method according to claim 31, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

136. (Canceled)

137. (Currently Amended) The method according to claim 31, wherein each of the first and second leveling films comprises an inorganic spin on glass material.

138. (Canceled)

139. (Previously Presented) The method according to claim 33, wherein the wiring is formed by a sputtering method.

140. (Previously Presented) The method according to claim 33, wherein the wiring comprises aluminum.

141. (Previously Presented) The method according to claim 33, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

142. (Canceled)

143. (Currently Amended) The method according to claim 33, wherein the ~~silicon nitride~~

second insulating film has a thickness of 50 to 500nm.

144. (Currently Amended) The method according to claim 33, wherein the ~~silicon nitride~~
second insulating film has a thickness of 200 to 300nm.

145. (Currently Amended) The method according to claim 33, wherein the first leveling film
has a thickness of 0.1 μ m to 1.5 μ m.

146. (Canceled)

147. (Currently Amended) The method according to claim 33, wherein each of the first and
second leveling films comprises an inorganic spin on glass material.

148. (Canceled)

149. (Currently Amended) A method of fabricating a ~~display~~ semiconductor device
comprising the steps of:

~~forming a semiconductor film over a substrate;~~

~~forming an interlayer insulating film over the semiconductor film;~~

~~forming a wiring connecting to the semiconductor film through a first hole in the interlayer
insulating film on the interlayer insulating film;~~

forming a wiring on a first insulating film;

forming a second insulating film comprising silicon nitride oxide over said wiring film

~~directly formed on the wiring;~~

forming a first leveling film ~~formed~~ by a spin coating method on the ~~silicon nitride oxide~~
second insulating film; and

forming a second leveling film on the first leveling film by a spin coating method, wherein
said second leveling film is thicker than said first leveling film.

~~forming a pixel electrode over the leveling film connecting to the wiring through a second~~
~~hole formed in the silicon nitride oxide film and the leveling film.~~

150. (Previously Presented) The method according to claim 149, wherein the wiring is formed by a sputtering method.

151. (Previously Presented) The method according to claim 149, wherein the wiring comprises aluminum.

152. (Previously Presented) The method according to claim 149, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

153. (Canceled)

154. (Currently Amended) The method according to claim 149, wherein the ~~silicon nitride oxide~~ second insulating film has a thickness of 50 to 500nm.

155. (Currently Amended) The method according to claim 149, wherein the ~~silicon-nitride oxide~~ second insulating film has a thickness of 200 to 300nm.

156. (Currently Amended) The method according to claim 149, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

157. (Canceled)

158. (Currently Amended) The method according to claim 149, wherein each of the first and second leveling films comprises an inorganic spin on glass material.

159-160. (Canceled)

161. (Currently Amended) A method of fabricating a semiconductor display device comprising the steps of:

~~forming a semiconductor film over a substrate;~~

~~forming an interlayer insulating film over the semiconductor film;~~

~~forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;~~

~~forming a silicon-nitride oxide film covering a surface of the wiring;~~

forming an insulating film over a wiring;

forming a first leveling film ~~formed~~ by a spin coating method on the ~~silicon-nitride oxide insulating~~ film; and

forming a second leveling film on the first leveling film by a spin coating method, wherein said second leveling film is thicker than said first leveling film.

~~forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film.~~

162. (Previously Presented) The method according to claim 161, wherein the wiring is formed by a sputtering method.

163. (Previously Presented) The method according to claim 161, wherein the wiring comprises aluminum.

164. (Previously Presented) The method according to claim 161, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

165. (Canceled)

166. (Currently Amended) The method according to claim 161, wherein the ~~silicon nitride oxide~~ second insulating film has a thickness of 50 to 500nm.

167. (Currently Amended) The method according to claim 161, wherein the ~~silicon nitride oxide~~ second insulating film has a thickness of 200 to 300nm.

168. (Currently Amended) The method according to claim 161, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

169. (Canceled)

170. (Currently Amended) The method according to claim 161, wherein each of the first and second leveling films comprises an inorganic spin on glass material.

171-172. (Canceled)

173. (Currently Amended) A method of fabricating a ~~display~~ semiconductor device comprising the steps of:

~~forming a semiconductor film over a substrate;~~

~~forming an interlayer insulating film over the semiconductor film;~~

~~forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;~~

forming a wiring on a first insulating film;

~~forming a second insulating film comprising silicon nitride over said wiring oxide film deposited on the wiring;~~

~~forming a first leveling film formed by a spin coating method on the silicon nitride oxide second insulating film; and~~

forming a second leveling film on said first leveling film by spin coating, wherein said second leveling film is thicker than said first leveling film.

~~forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film.~~

174. (Previously Presented) The method according to claim 173, wherein the wiring is formed by a sputtering method.

175. (Previously Presented) The method according to claim 173, wherein the wiring comprises aluminum.

176. (Previously Presented) The method according to claim 173, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

177. (Canceled)

178. (Currently Amended) The method according to claim 173, wherein the ~~silicon nitride oxide~~ second insulating film has a thickness of 50 to 500nm.

179. (Currently Amended) The method according to claim 173, wherein the ~~silicon nitride oxide~~ second insulating film has a thickness of 200 to 300nm.

180. (Currently Amended) The method according to claim 173, wherein the first leveling film has a thickness of 0.1 μ m to 1.5 μ m.

181. (Canceled)

182. (Currently Amended) The method according to claim 173, wherein each of the first and second leveling films comprises an inorganic spin on glass material.

183-184. (Canceled)

185. (New) The method according to claim 10 wherein each of said first and second leveling films comprises a resin.

186. (New) The method according to claim 10 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.

187. (New) The method according to claim 31 wherein each of said first and second leveling films comprises a resin.

188. (New) The method according to claim 33 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.

189. (New) The method according to claim 33 wherein each of said first and second leveling films comprises a resin.

190. (New) The method according to claim 33 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.

191. (New) The method according to claim 149 wherein each of said first and second leveling films comprises a resin.

192. (New) The method according to claim 149 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.

193. (New) The method according to claim 161 wherein each of said first and second leveling films comprises a resin.

194. (New) The method according to claim 161 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.

195. (New) The method according to claim 173 wherein each of said first and second leveling films comprises a resin.

196. (New) The method according to claim 173 wherein each of said first and second leveling films comprises a material selected from the group consisting of phosphosilicate glass, borosilicate glass and borophosphosilicate glass.